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December 2014



FCP110N65F N-Channel SuperFET[®] II FRFET[®] MOSFET 650 V, 35 A, 110 m Ω

Features

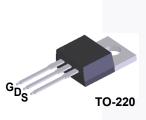
- 700 V @ T_J = 150°C
- Typ. R_{DS(on)} = 96 mΩ (Typ.)
- Ultra Low Gate Charge (Typ. Q_g = 98 nC)
- Low Effective Output Capacitance (Typ. Coss(eff.) = 464 pF)
- 100% Avalanche Tested
- RoHS Compliant

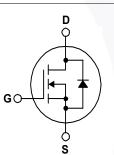
Applications

- LCD / LED / PDP TV
 Telecom / Server Power Supplies
- Solar Inverter
 AC DC Power Supply

Description

SuperFET[®] II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications. SuperFET II FRFET[®] MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		FCP110N65F	Unit			
V _{DSS}	Drain to Source Voltage	Drain to Source Voltage			V	
V _{GSS}		- DC		±20	V	
	Gate to Source Voltage	- AC	(f > 1 Hz)	±30	v	
ID	Drain Current	- Continuous (T _C = 25 ^o C)		35	Α	
	Drain Current	- Continuous (T _C = 100 ^o C)		24	A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	105	А	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)			809	mJ	
I _{AR}	Avalanche Current	(Note 1)	8	А		
E _{AR}	Repetitive Avalanche Energy	(Note 1)	3.57	mJ		
dv/dt	MOSFET dv/dt			100	V/ns	
	Peak Diode Recovery dv/dt (Note 3)			50		
P _D	Dower Dissinction	(T _C = 25 ^o C)		357	W	
	Power Dissipation	- Derate Above 25°C		2.86	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

Thermal Characteristics

Symbol	Parameter	FCP110N65F	Unit		
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max. 0.35				
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	°C/W		

	nber	Top Mark	Package Packing Method Reel Size		Тар	e Width	Qua	ntity	
			TO-220	Tube	N/A		N/A	50 units	
=loctrica	l Char	acteristics T _C :	- 25 ⁰ C unloss	othonwise noted					
Symbol		Parameter	- 25 C unless	Test Conditi	ions	Min.	Тур.	Max.	Unit
-	toristic			Test conditi			Typ.	Max.	onn
	haracteristics			V _{GS} = 0 V, I _D = 10 mA, T _J = 25°C		650	-	_	
BV _{DSS}	Drain to Source Breakdown Voltage		/oltage	$V_{GS} = 0 V, I_D = 10 \text{ mA}, T_J = 150^{\circ}\text{C}$		700	-	-	V
ΔBV _{DSS} / ΔT _J		reakdown Voltage Temperature oefficient		$I_D = 10 \text{ mA}, \text{ Referenced to } 25^{\circ}\text{C}$		-	0.72	-	V/ºC
I _{DSS}	Zero Ga	Zero Gate Voltage Drain Current		V_{DS} = 650 V, V_{GS} = 0		-	-	10	μA
055				V _{DS} = 520 V, T _C = 125 ^o C		-	110	-	
I _{GSS}	Gate to	Body Leakage Curre	nt	$V_{GS} = \pm 20 V, V_{DS} = 0$	V	-	-	±100	nA
On Charac	teristics	6							
V _{GS(th)}	Gate Threshold Voltage			$V_{GS} = V_{DS}, I_{D} = 3.5 \text{ mA}$			-	5	V
R _{DS(on)}	Static D	atic Drain to Source On Resistance		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 17.5 \text{ A}$		-	96	110	mΩ
9 _{FS}	Forward	vard Transconductance		V _{DS} = 20 V, I _D = 17.5 A		-	30	-	S
Dynamic C	haracte	eristics							
C _{iss}	Input Capacitance				-	3680	4895	pF	
C _{oss}	-	Capacitance		$V_{\rm DS} = 100 \text{ V}, \text{ V}_{\rm GS} = 0 \text{ V},$		-	110	145	pF
C _{rss}	-	Transfer Capacitanc	acitance f = 1 MHz		-	0.65	-	pF	
C _{oss}	Output 0	Capacitance		V _{DS} = 380 V, V _{GS} = 0 V, f = 1 MHz		-	65	-	pF
C _{oss(eff.)}	-	ive Output Capacitance		$V_{DS} = 0 V \text{ to } 400 V, V_{GS} = 0 V$		-	464	-	pF
Q _{g(tot)}		ite Charge at 10V		V _{DS} = 380 V, I _D = 17.5 A,		-	98	145	nC
Q _{gs}		Source Gate Charge		$V_{GS} = 10 V$		-	20	-	nC
Q _{gd}	Gate to	Drain "Miller" Charge			(Note 4)	-	43	-	nC
ESR	Equivale	ent Series Resistance	1	f = 1 MHz		-	0.7	-	Ω
Switching	Charact	teristics							
t _{d(on)}	-	Delay Time				-	31	72	ns
t _r		Turn-On Rise Time		V _{DD} = 380 V, I _D = 17.5 A,		-	21	52	ns
t _{d(off)}	Turn-Off Delay Time			$V_{GS} = 10 \text{ V}, \text{ R}_{g} = 4.7 \Omega$ (Note 4)		-	89	188	ns
t _f		urn-Off Fall Time				-	5.7	21	ns
						1.	1		
Jrain-Sour	T	le Characteristic							
l _S	Maximum Continuous Drain to Source Diode F					-	-	35	A
SM		n Pulsed Drain to So			-	-	-	105	A
V _{SD}		to Source Diode Forward Voltage		V _{GS} = 0 V, I _{SD} = 17.5 A		-	-	1.2	V
t _{rr}		Recovery Time		$V_{GS} = 0 V, I_{SD} = 17.5 J$	А,	-	133	-	ns
Q _{rr}	Reverse	Recovery Charge		$dI_F/dt = 100 A/\mu s$		-	0.67	-	μC

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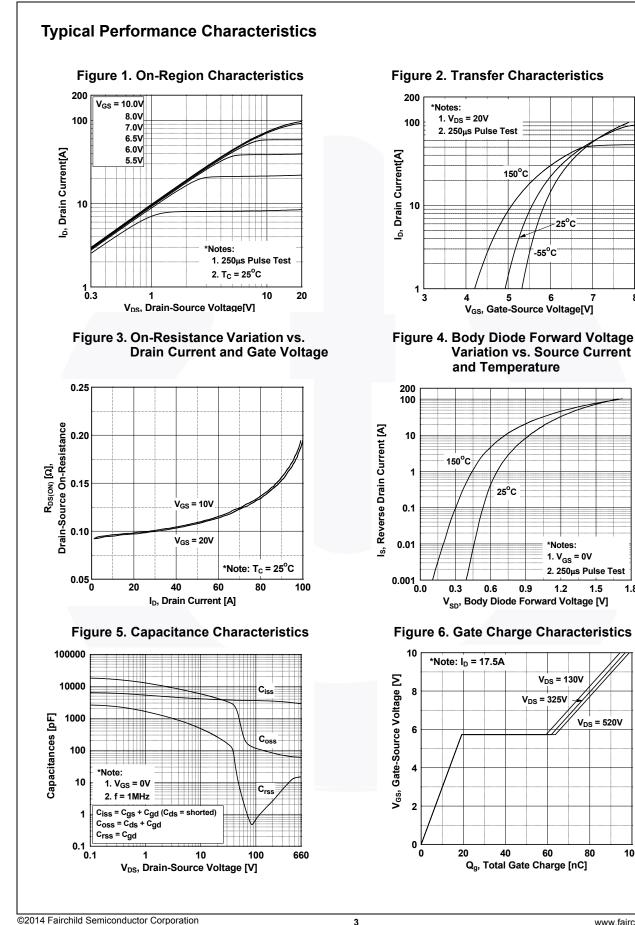
1.5

V_{DS} = 520V

80

1.8

8

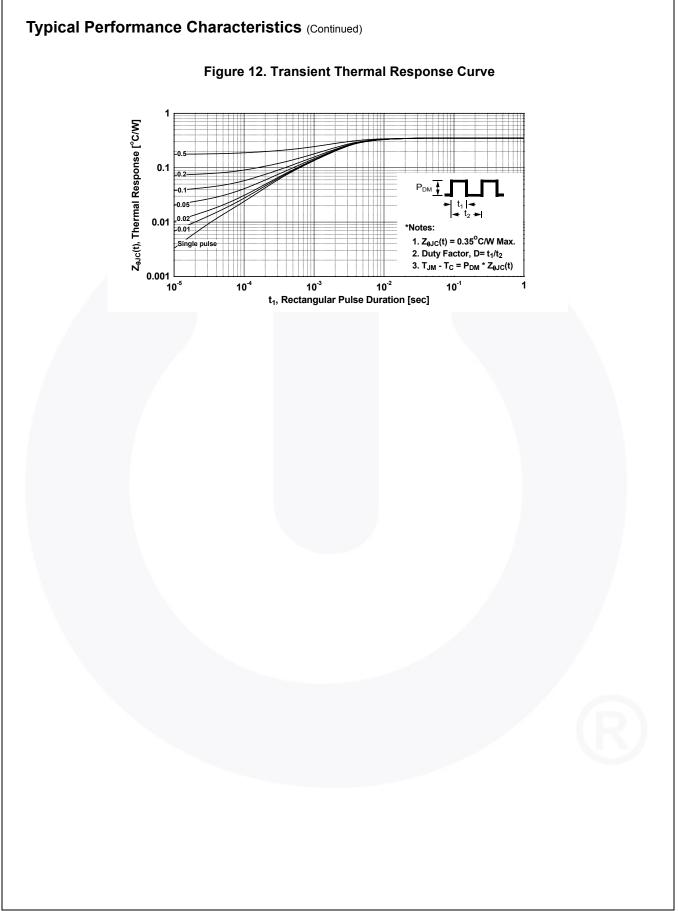


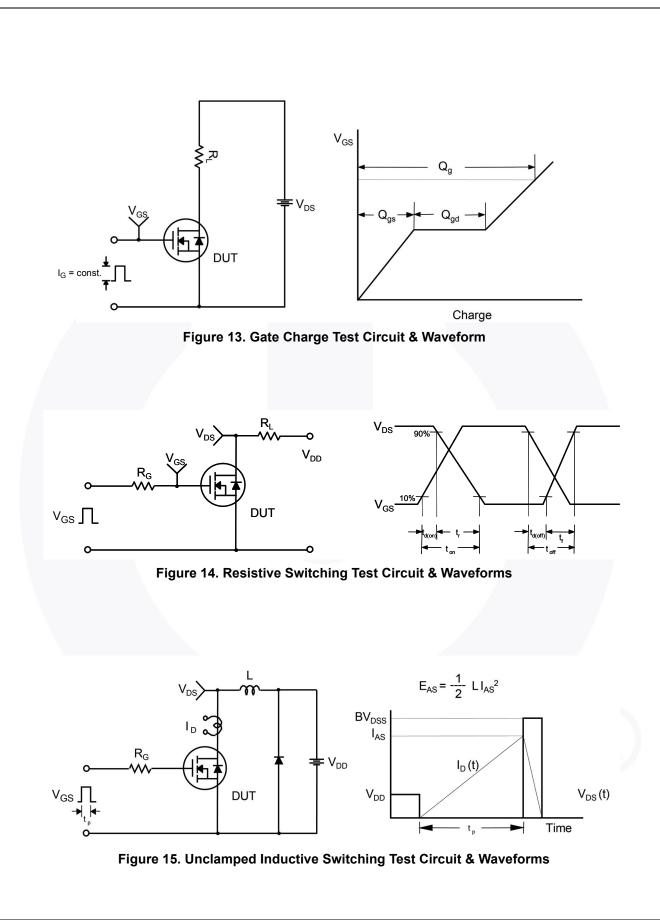
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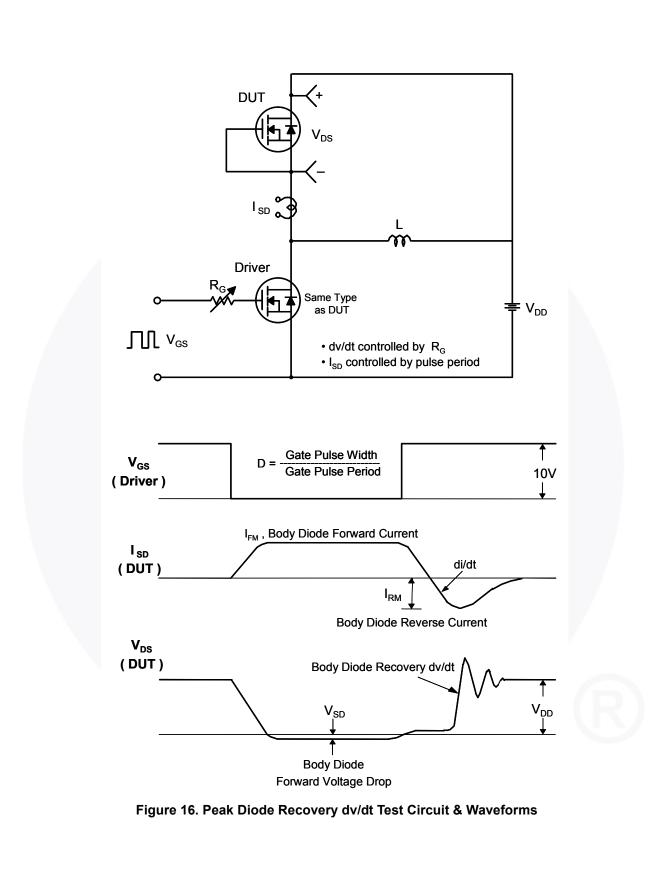
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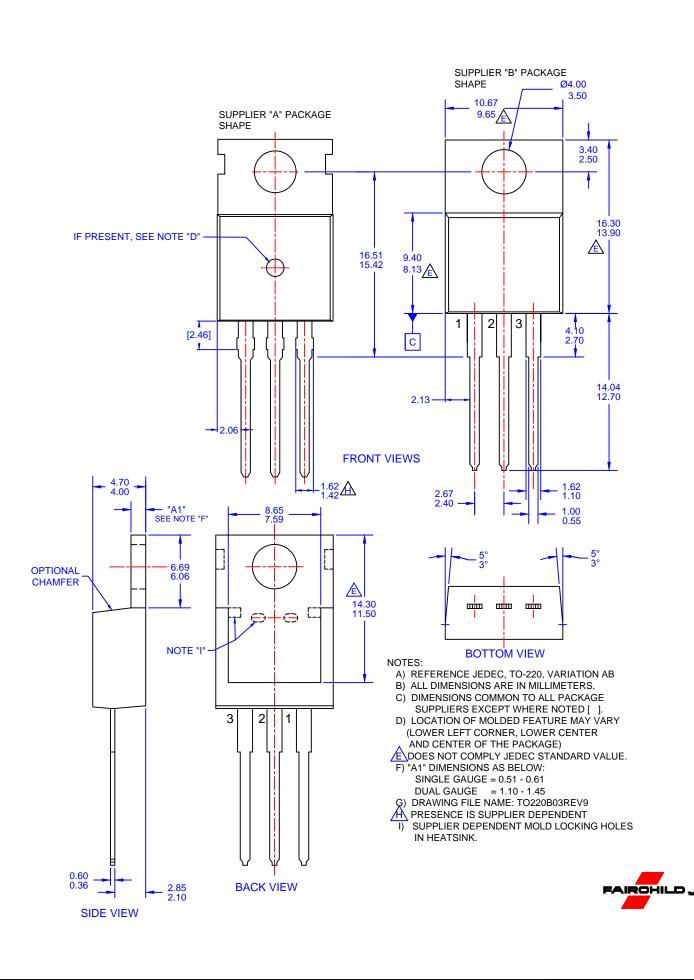
Typical Performance Characteristics (Continued) Figure 7. Breakdown Voltage Variation Figure 8. On-Resistance Variation vs. Temperature vs. Temperature 2.5 1.15 *Notes: *Notes: Drain-Source Breakdown Voltage 1. V_{GS} = 10V 1. V_{GS} = 0V Drain-Source On-Resistance 0. 2.1 0. 2.1 2. I_D = 17.5A 2. I_D = 10mA 1.10 R_{DS(on)}, [Normalized] BV_{DSS}, [Normalized] 1.05 1.00 0.95 0.5 └─ -100 0.90 L -100 -50 0 50 100 150 200 0 50 100 150 200 -50 T_J, Junction Temperature [°C] T_J, Junction Temperature [^oC] Figure 9. Maximum Safe Operating Area Figure 10. Maximum Drain Current vs. Case Temperature 300 40 100 10µs 100µs l_b, Drain Current [A] 30 I_D, Drain Current [A] 10 1ms 20 DC 1 **Operation in This Area** is Limited by R DS(on) Notes: 10 1. T_C = 25°C 0.1 2. T_J = 150^oC 3. Single Pulse 0.01 └─ 0.1 0 ∟ 25 10 100 1000 50 75 100 125 150 1 T_c, Case Temperature [°C] V_{DS}, Drain-Source Voltage [V] Figure 11. Eoss vs. Drain to Source Voltage 20 16 Е_{oss}, [µJ] 12 8 4 0 132 264 396 528 V_{DS}, Drain to Source Voltage [V] 660





FCP110N65F — N-Channel SuperFET[®] II FRFET[®] MOSFET





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